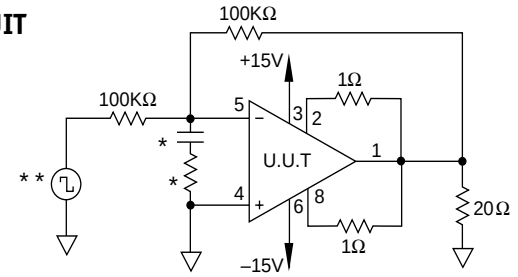
SG	PARAMETER	SYMBOL	TEMP.	POWER	TEST CONDITIONS	MIN	MAX	UNITS
1	Quiescent current	I_Q	25°C	±40V	V_{IN} = 0, A_V = 100, R_{CL} = .1Ω		30	mA
1	Input offset voltage	V_{OS}	25°C	±40V	V_{IN} = 0, A_V = 100		±6	mV
1	Input offset voltage	V_{OS}	25°C	±10V	V_{IN} = 0, A_V = 100		±12	mV
1	Input offset voltage	V_{OS}	25°C	±45V	V_{IN} = 0, A_V = 100		±7	mV
1	Input bias current, +IN	$+I_B$	25°C	±40V	V_{IN} = 0		±30	nA
1	Input bias current, –IN	$–I_B$	25°C	±40V	V_{IN} = 0		±30	nA
1	Input offset current	I_{OS}	25°C	±40V	V_{IN} = 0		±30	nA
3	Quiescent current	I_Q	–55°C	±40V	V_{IN} = 0, A_V = 100, R_{CL} = .1Ω		75	mA
3	Input offset voltage	V_{OS}	–55°C	±40V	V_{IN} = 0, A_V = 100		±11.2	mV
3	Input offset voltage	V_{OS}	–55°C	±10V	V_{IN} = 0, A_V = 100		±17.2	mV
3	Input offset voltage	V_{OS}	–55°C	±45V	V_{IN} = 0, A_V = 100		±12.2	mV
3	Input bias current, +IN	$+I_B$	–55°C	±40V	V_{IN} = 0		±115	nA
3	Input bias current, –IN	$–I_B$	–55°C	±40V	V_{IN} = 0		±115	nA
3	Input offset current	I_{OS}	–55°C	±40V	V_{IN} = 0		±115	nA
2	Quiescent current	I_Q	125°C	±40V	V_{IN} = 0, A_V = 100, R_{CL} = .1Ω		30	mA
2	Input offset voltage	V_{OS}	125°C	±40V	V_{IN} = 0, A_V = 100		±12.5	mV
2	Input offset voltage	V_{OS}	125°C	±10V	V_{IN} = 0, A_V = 100		±18.5	mV
2	Input offset voltage	V_{OS}	125°C	±45V	V_{IN} = 0, A_V = 100		±13.5	mV
2	Input bias current, +IN	$+I_B$	125°C	±40V	V_{IN} = 0		±70	nA
2	Input bias current, –IN	$–I_B$	125°C	±40V	V_{IN} = 0		±70	nA
2	Input offset current	I_{OS}	125°C	±40V	V_{IN} = 0		±70	nA
4	Output voltage, I_O = 5A	V_O	25°C	±18V	R_L = 2.07Ω	10		V
4	Output voltage, I_O = 80mA	V_O	25°C	±45V	R_L = 500Ω	40		V
4	Output voltage, I_O = 2A	V_O	25°C	±30V	R_L = 12Ω	24		V
4	Current limits	I_{CL}	25°C	±17V	R_L = 12Ω, R_{CL} = 1Ω	.6	.89	A
4	Stability/noise	E_N	25°C	±40V	R_L = 100Ω, A_V = 1, C_L = .33nF		1	mV
4	Slew rate	SR	25°C	±40V	R_L = 500Ω	2	10	V/µs
4	Open loop gain	A_{OL}	25°C	±40V	R_L = 500Ω, F = 10Hz	96		dB
4	Common mode rejection	CMR	25°C	±15V	R_L = 500Ω, F = DC, V_{CM} = ±9V	74		dB
6	Output voltage, I_O = 5A	V_O	–55°C	±18V	R_L = 2.07Ω	10		V
6	Output voltage, I_O = 80mA	V_O	–55°C	±45V	R_L = 500Ω	40		V
6	Output voltage, I_O = 2A	V_O	–55°C	±30V	R_L = 12Ω	24		V
6	Stability/noise	E_N	–55°C	±40V	R_L = 100Ω, A_V = 1, C_L = .33nF		1	mV
6	Slew rate	SR	–55°C	±40V	R_L = 500Ω	2	10	V/µs
6	Open loop gain	A_{OL}	–55°C	±40V	R_L = 500Ω, F = 10Hz	96		db
6	Common mode rejection	CMR	–55°C	±15V	R_L = 500Ω, F = DC, V_{CM} = ±9V	74		dB
5	Output voltage, I_O = 3A	V_O	125°C	±14.3V	R_L = 2.07Ω	6.3		V
5	Output voltage, I_O = 80mA	V_O	125°C	±45V	R_L = 500Ω	40		V
5	Output voltage, I_O = 2A	V_O	125°C	±30V	R_L = 12Ω	24		V
5	Stability/noise	E_N	125°C	±40V	R_L = 100Ω, A_V = 1, C_L = .33nF		1	mV
5	Slew rate	SR	125°C	±40V	R_L = 500Ω	2	10	V/µs
5	Open loop gain	A_{OL}	125°C	±40V	R_L = 500Ω, F = 10Hz	96		dB
5	Common mode rejection	CMR	125°C	±15V	R_L = 500Ω, F = DC, V_{CM} = ±9V	74		dB

BURN IN CIRCUIT



* These components are used to stabilize device due to poor high frequency characteristics of burn in board.

** Input signals are calculated to result in internal power dissipation of approximately 2.1W at case temperature = 125°C.

